



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

NPN Digital Silicon Transistor

VOLTAGE 50 Volts CURRENT 100 mAmpere

Lead free devices

CHDTC124GKPT

APPLICATION

- * Switching circuit, Inverter, Interface circuit, Driver circuit.

FEATURE

- * Small surface mounting type. (SC-59/SOT-346)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.
- * Internal isolated NPN transistors in one package.
- * Built in bias resistor($R_1=22\text{k}\Omega$, Typ.)

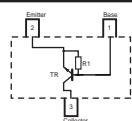
CONSTRUCTION

- * One NPN transistors and bias of thin-film resistors in one package.

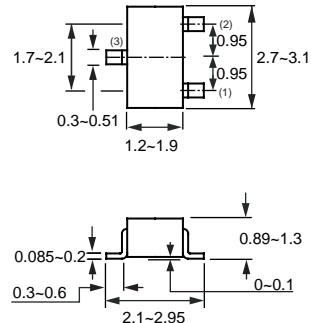
MARKING

GKB

CIRCUIT



SC-59/SOT-346



Dimensions in millimeters

SC-59/SOT-346

LIMITING VALUES

In accordance with the Absolute Maximum Rating System .

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-Base voltage		50	V
V_{CEO}	Collector-Emitter voltage		50	V
V_{EBO}	Emitter-Base voltage		5	V
$I_C(\text{Max.})$	Collector current		100	mA
P_D	Power dissipation	$T_{\text{amb}} \leq 25^\circ\text{C}$, Note 1	200	mW
T_{STG}	Storage temperature		-55 +150	°C
T_J	Junction temperature		-55 +150	°C
$R_{\theta J-S}$	Thermal resistance , Note 1	junction - soldering point	140	°C/W

Note

- Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHDTC124GKPT)

CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCBO	Collector-Base breakdown voltage	$I_c=50\mu\text{A}$	50.0	—	—	V
BVCEO	Collector-Emitter breakdown voltage	$I_c=1\text{mA}$	50.0	—	—	V
BVEBO	Emitter-Base breakdown voltage	$I_e=330\mu\text{A}$	5.0	—	—	V
VCE(sat)	Collector-Emitter Saturation voltage	$I_c=10\text{mA}; I_b=0.5\text{mA}$	—	—	0.3	V
I_{CBO}	Collector-Base current	$V_{CB}=50\text{V}$	—	—	0.5	μA
I_{EBO}	Emitter-Base current	$V_{EB}=4\text{V}$	140	—	260	μA
h_{FE}	DC current gain	$I_c=5\text{mA}; V_{CE}=5.0\text{V}$	56	—	—	
R_1	Input resistor		15.4	22	28.6	$\text{k}\Omega$
f_T	Transition frequency	$I_e=-5\text{mA}, V_{CE}=10.0\text{V}$ $f=100\text{MHz}$	—	250	—	MHz

Note

1. Pulse test: $t_p \leq 300\mu\text{s}; \delta \leq 0.02$.